
2SB1059

Silicon PNP Epitaxial

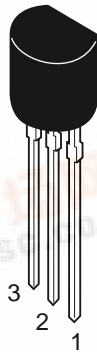
HITACHI

Application

- Low frequency power amplifier
- Complementary pair with 2SD1490

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SB1059

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-70	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-6	V
Collector current	I_C	-1	A
Collector power dissipation	P_C	0.75	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

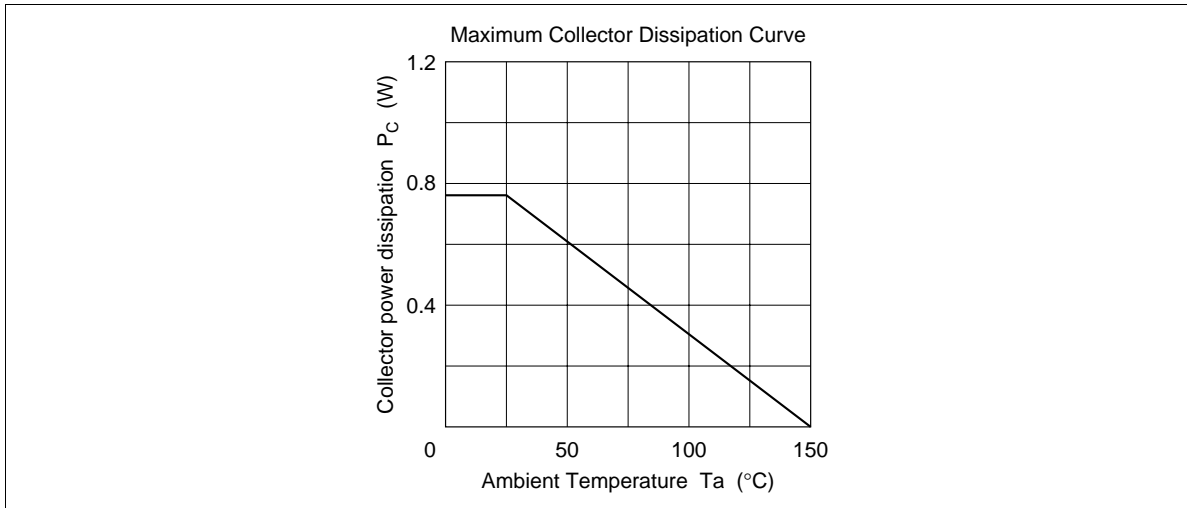
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	μA	$V_{CB} = -55 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.2	μA	$V_{EB} = -6 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	320		$V_{CE} = -2 \text{ V}, I_C = -0.1 \text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.6	V	$I_C = -1 \text{ A}, I_B = -0.1 \text{ A}$
Gain bandwidth product	f_T	—	65	—	MHz	$V_{CE} = -2 \text{ V}, I_C = -10 \text{ mA}$
Collector output capacitance	C_{ob}	—	35	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SB1059 is grouped by h_{FE} as follows.

B	C
100 to 200	160 to 320

See characteristic curves of 2SB740.



Unit: mm

